

[Abstract]

Provided is a cleaning solution composition which, when cleaning the surface of a semiconductor substrate or glass substrate, does not damage SiO_2 , Si_3N_4 , Si, and the like forming a layer on the substrate surface, can be used under processing conditions applicable to a brush scrub cleaning chamber equipped with a CMP apparatus, and can efficiently remove compounds derived from abrasive particles in a slurry. This cleaning solution composition for cleaning the surface of a semiconductor substrate or glass substrate contains: one or two or more fluorine atom-containing inorganic acids or salts thereof; water; one or two or more reducing agents; and one or two or more anionic surfactants, and has a hydrogen ion concentration (pH) of less than 7.

[No suitable drawing]